

UHF POWER MOS TRANSISTOR

DESCRIPTION:

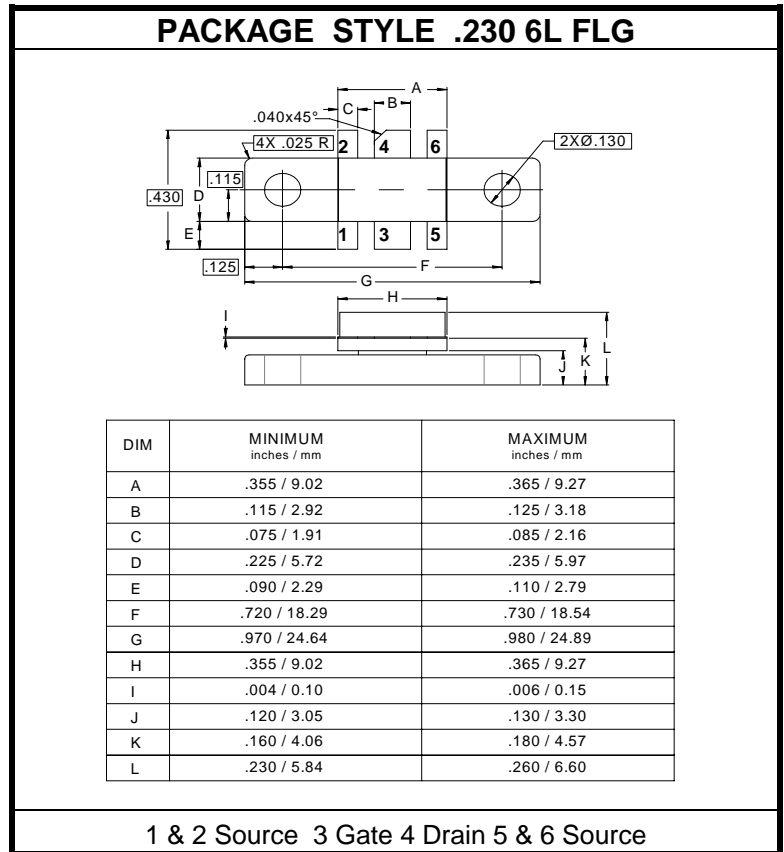
The **ASI BLF522** is Designed for communications transmitter applications in the UHF frequency range.

FEATURES:

- Designed for broadband operation.
- High power gain
- **Omnigold™** Metalization System

MAXIMUM RATINGS

V_{DS}	50 V
$\pm V_{GS}$	30 V
V_{DG}	50 V
I_D	1.6 A
P_{DISS}	30 W @ $T_C = 25\text{ }^\circ\text{C}$
T_J	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
T_{STG}	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$
θ_{JC}	6.0 $^\circ\text{C/W}$


CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$I_{DS} = 20\text{ mA}$	40			V
I_{DSS}	$V_{DS} = 12.5\text{ V}$			0.4	mA
I_{GSS}	$V_{DS} = 0\text{ V}$ $\pm V_{GS} = 30\text{ V}$			1.0	μA
V_{GS}	$V_{GS} = 40\text{ V}$ $I_{DS} = 40\text{ mA}$	1.0		7.0	V
g_M	$V_{DS} = 10\text{ V}$ $V_{GS} = 5.0\text{ V}$		0.4		Mho
$R_{DS(on)}$	$V_{GS} = 20\text{ V}$ $I_{DS} = 3.2\text{ A}$		1.2		Ω
I_{Dsat}	$V_{DS} = 10\text{ V}$ $V_{GS} = 20\text{ V}$		4.6		A



C_{iss}	$V_{DS} = 12.5 V$	$V_{GS} = 0 V$	$f = 1.0 MHz$		15		
C_{oss}					16		pF
C_{rss}					2.4		
P_G	$V_{DS} = 12.5 V$	$I_{DQ} = 5.0 W$	$f = 850 GHz$	10			dB
η_D					50		